



30N15-ML

Preliminary

Power MOSFET

30A, 150V N-CHANNEL POWER MOSFET

DESCRIPTION

The UTC **30N15-ML** is a N-channel enhancement MOSFET using UTC's advanced technology to provide the customers with perfect $R_{DS(ON)}$, high switching speed, high current capacity and low gate charge.

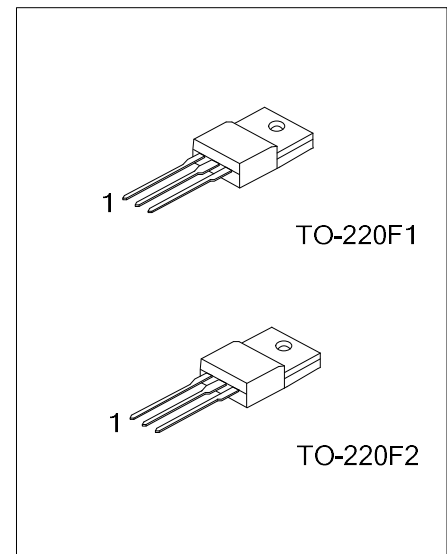
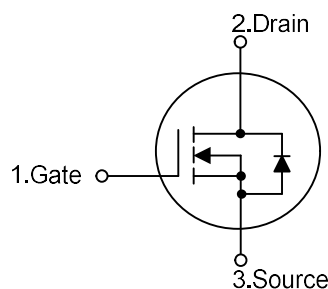
The UTC **30N15-ML** is universally applied in low voltage such as automotive, high efficiency switching for AC/DC converters and DC motor control, etc.

FEATURES

* $R_{DS(ON)} \leq 70 \text{ m}\Omega$ @ $V_{GS}=10\text{V}$, $I_D=15\text{A}$

* High Switching Speed

SYMBOL



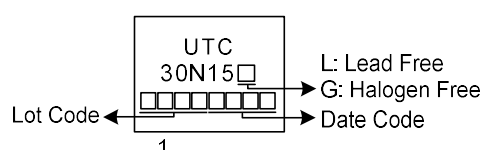
ORDERING INFORMATION

Ordering Number		Package	Pin Assignment			Packing
Lead Free	Halogen Free		1	2	3	
30N15L-TF1-T	30N15G-TF1-T	TO-220F1	G	D	S	Tube
30N15L-TF2-T	30N15G-TF2-T	TO-220F2	G	D	S	Tube

Note: Pin Assignment: G: Gate D: Drain S: Source

30N15G-TF1-T (1) Packing Type (2) Package Type (3) Green Package	(1) T: Tube (2) TF1: TO-220F1, TF2: TO-220F2 (3) G: Halogen Free and Lead Free, L: Lead Free
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MARKING



■ **ABSOLUTE MAXIMUM RATINGS** ($T_C=25^{\circ}\text{C}$, unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT
Drain-Source Voltage		V_{DS}	150	V
Gate-Source Voltage		V_{GS}	± 30	V
Continuous Drain Current	Continuous	I_D	30	A
	Pulsed	I_{DM}	60	A
Single Pulsed Avalanche Current		I_{AS}	9.8	A
Single Pulsed Avalanche Energy		E_{AS}	1440	mJ
Peak Diode Recovery dv/dt (Note 4)		dv/dt	5.1	V/ns
Power Dissipation		P_D	50	W
Junction Temperature		T_J	+150	$^{\circ}\text{C}$
Storage Temperature		T_{STG}	-55 ~ +150	$^{\circ}\text{C}$

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied.

2. Repetitive Rating : Pulse width limited by maximum junction temperature.

3. $L=30\text{mH}$, $I_{AS}=9.8\text{A}$, $V_{DD}=50\text{V}$, $R_G=25\Omega$, Starting $T_J = 25^{\circ}\text{C}$

4. $I_{SD}\leq 30\text{A}$, $di/dt\leq 200\text{A}/\mu\text{s}$, $V_{DD}\leq BV_{DS}$, Starting $T_J = 25^{\circ}\text{C}$

■ **THERMAL DATA**

PARAMETER	SYMBOL	RATING	UNIT
Junction to Ambient	θ_{JA}	62.5	$^{\circ}\text{C}/\text{W}$
Junction to Case	θ_{JC}	2.5	$^{\circ}\text{C}/\text{W}$

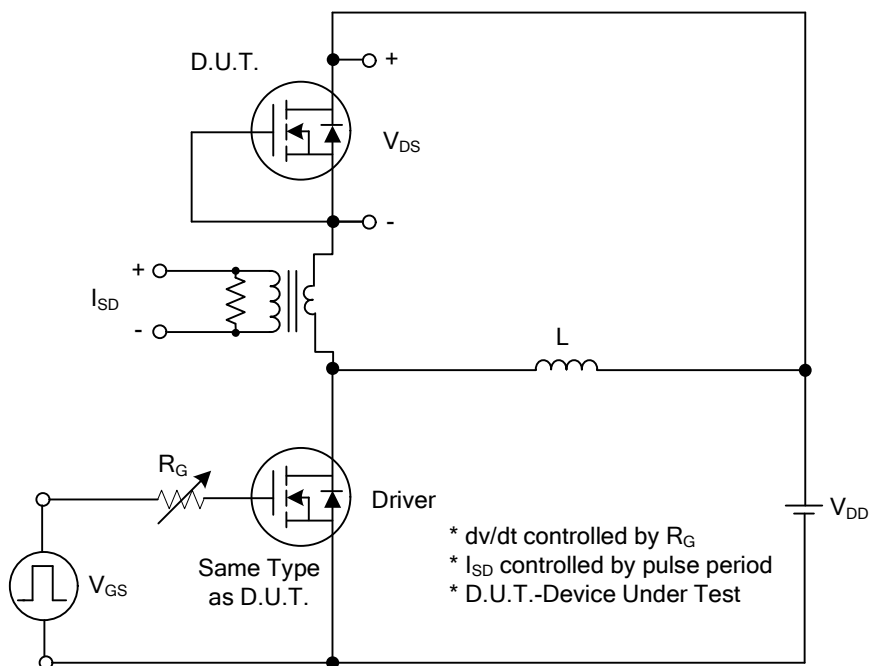
■ **ELECTRICAL CHARACTERISTICS** ($T_J=25^\circ\text{C}$, unless otherwise specified)

PARAMETER		SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS							
Drain-Source Breakdown Voltage		BV _{DSS}	I _D =250μA, V _{GS} =0V	150			V
Drain-Source Leakage Current		I _{DSS}	V _{DS} =150V, V _{GS} =0V			10	μA
Gate-Source Leakage Current	Forward	I _{GSS}	V _{GS} =+30V, V _{DS} =0V			+100	nA
	Reverse		V _{GS} =-30V, V _{DS} =0V			-100	nA
ON CHARACTERISTICS							
Gate Threshold Voltage		V _{GS(TH)}	V _{DS} =V _{GS} , I _D =250μA	2.0		4.0	V
Static Drain-Source On-State Resistance		R _{DS(ON)}	V _{GS} =10V, I _D =15A			70	mΩ
DYNAMIC PARAMETERS							
Input Capacitance		C _{ISS}	V _{GS} =0V, V _{DS} =25V, f=1.0MHz		2040		pF
Output Capacitance		C _{OSS}			320		pF
Reverse Transfer Capacitance		C _{RSS}			15		pF
SWITCHING PARAMETERS							
Total Gate Charge		Q _G	V _{DS} =120V, V _{GS} =10V, I _D =30A I _G =1mA (Note 1, 2)		46		nC
Gate to Source Charge		Q _{GS}			17		nC
Gate to Drain Charge		Q _{GD}			11		nC
Turn-ON Delay Time		t _{D(ON)}	V _{DD} =100V, V _{GS} =10V, I _D =30A, R _G =25Ω (Note 1, 2)		26		ns
Rise Time		t _R			21		ns
Turn-OFF Delay Time		t _{D(OFF)}			98		ns
Fall-Time		t _F			24		ns
SOURCE- DRAIN DIODE RATINGS AND CHARACTERISTICS							
Maximum Body-Diode Continuous Current		I _S				30	A
Maximum Body-Diode Pulsed Current		I _{SM}				60	A
Drain-Source Diode Forward Voltage		V _{SD}	I _S =30A, V _{GS} =0V			1.4	V
Body Diode Reverse Recovery Time		t _{rr}	I _S =30A, V _{GS} =0V, dI _F /dt=100A/μs		120		ns
Reverse Recovery Charge		Q _{rr}	(Note 1)		0.55		μC

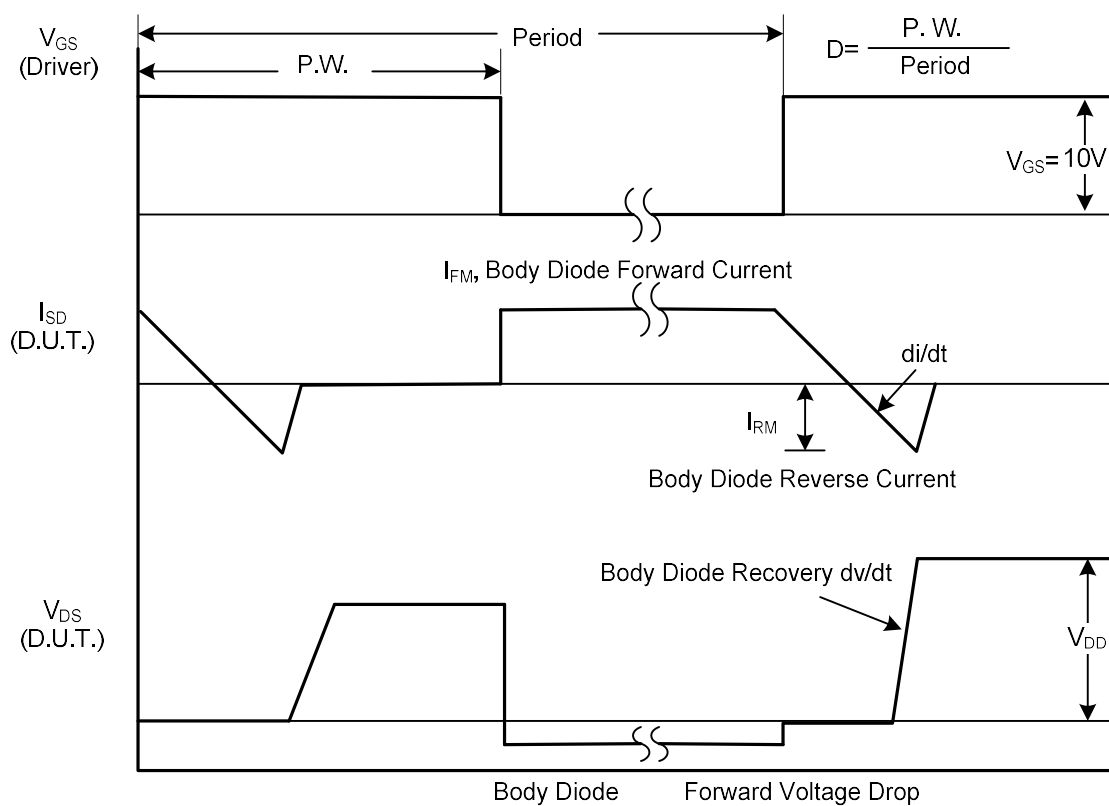
Notes: 1. Pulse Test: Pulse width $\leq 300\mu\text{s}$, Duty cycle $\leq 2\%$.

2. Essentially independent of operating temperature.

■ TEST CIRCUITS AND WAVEFORMS

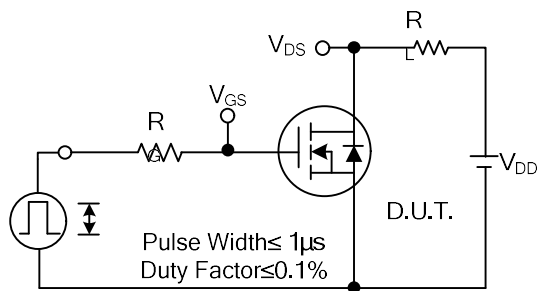


Peak Diode Recovery dv/dt Test Circuit

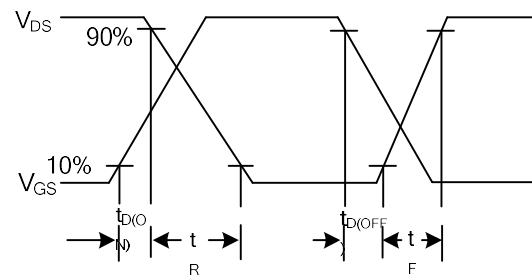


Peak Diode Recovery dv/dt Waveforms

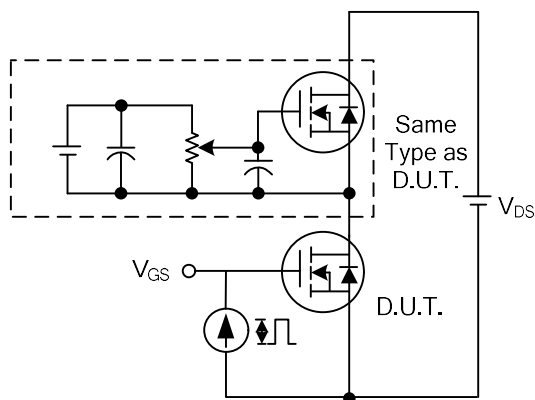
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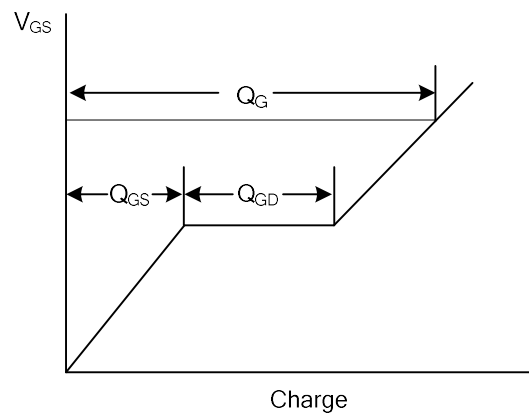
Switching Test Circuit



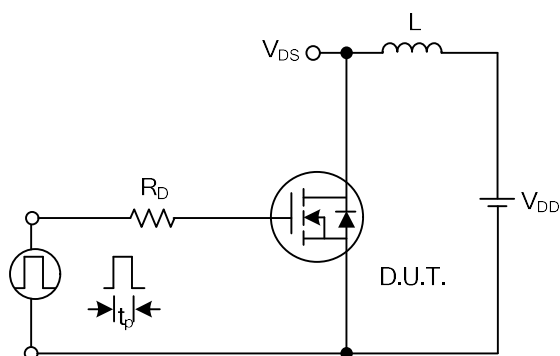
Switching Waveforms



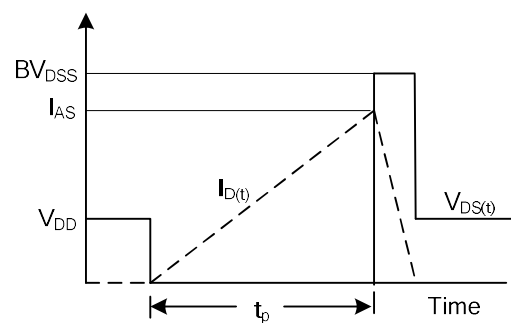
Gate Charge Test Circuit



Gate Charge Waveform



Unclamped Inductive Switching Test Circuit



Unclamped Inductive Switching Waveforms

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